TECHNICAL DATA SHEET DATASHEET 6187, Rev -

SILICON ULTRA-FAST RECOVERY EPITAXIAL RECTIFIER DIE

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Glass Passivated Epitaxial Diode with Mesa Structure
- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop and Low Reverse Current
- Electrically and Mechanically Stable during and after Packaging

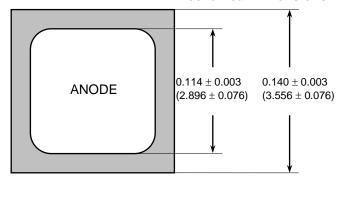
Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	300	V
Max. Output Current	I_0 50% duty cycle, rectangular wave form; $T_A = 25$ °C		25	А
Max. Junction Temperature	TJ	-	-55 to +175	°C
Max. Storage Temperature	T _{stg}	-	-55 to +200	°C
Reverse Recovery Time SD140UF300x35 SD140UF300x33	SD140UF300x35		35 33	ns

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	VF	25A, pulse, T _J = 25 °C	1.2	V
Max. Reverse Current	I _{R1}	V _R = V _{RWM} , pulse, T _J = 25 °C	5.0	μΑ
	I _{R2}	V _R = V _{RWM} , pulse, T _J = 125 °C	1	mA

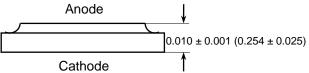
Mechanical Dimensions: In Inches (mm)



Bottom side metalization: Ti/Ni/Ag - 30 kÅ nominal

Top side metalization: Al - 25 kÅ minimum

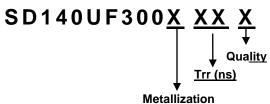
Bottom side is cathode, top side is anode.





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PART ORDERING INFORMATION:



Metallization (Example using SD140UF300x35):

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Suffix	Part Number	Description
Α	SD140UF300A35	Al top, Ag bottom
В	SD140UF300B35	Ag top, Ag bottom

Metallization (Example using SD140UF300x35):

Suffix	Part Number	Description
Н	SD140UF300A35H	Class H Element Eval
K	SD140UF300A35K	Class K Element Eval

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